

N-Channel NexFET™ Power MOSFETs

 Check for Samples: [CSD16301Q2](#)

FEATURES

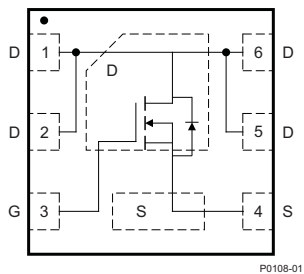
- Ultralow Q_g and Q_{gd}
- Low Thermal Resistance
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 2-mm × 2-mm Plastic Package

APPLICATIONS

- DC-DC Converters
- Battery and Load Management Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and load management applications. The SON 2x2 offers excellent thermal performance for the size of the package.

Figure 1. Top View


P0108-01

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25	V
Q_g	Gate Charge Total (-4.5V)	2	nC
Q_{gd}	Gate Charge Gate to Drain	0.4	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V$	27 mΩ
		$V_{GS} = 4.5V$	23 mΩ
		$V_{GS} = 8V$	19 mΩ
$V_{GS(th)}$	Threshold Voltage	1.1	V

ORDERING INFORMATION

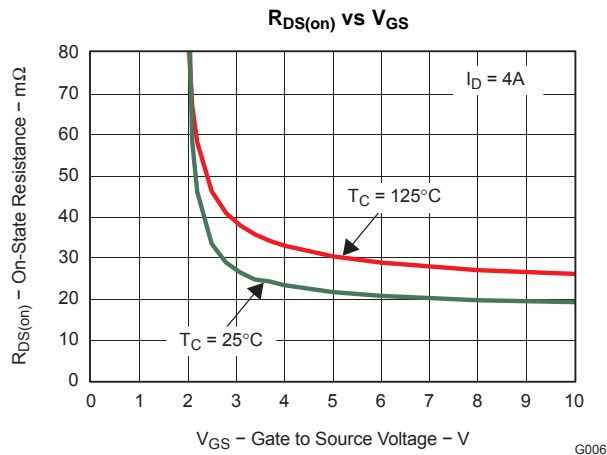
Device	Package	Media	Qty	Ship
CSD16301Q2	SON 2-mm × 2-mm Plastic Package	13-Inch Reel	3000	Tape and Reel
		7-Inch Reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

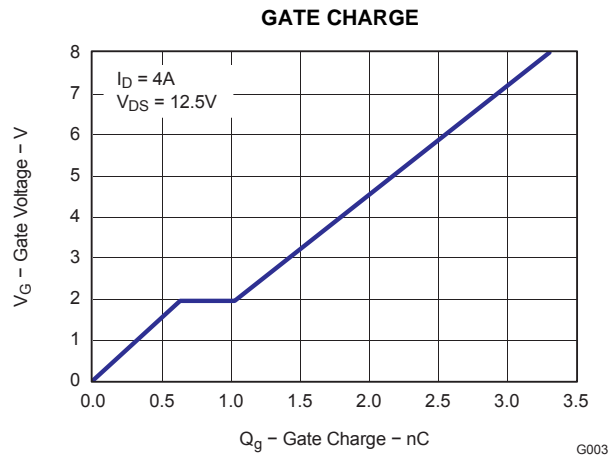
$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
I_D	Continuous Drain Current, $T_C = 25^\circ\text{C}$	5	A
	Continuous Drain Current ⁽¹⁾	5	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ ⁽²⁾	20	A
P_D	Power Dissipation ⁽¹⁾	2.3	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E_{AS}	Avalanche Energy, single pulse $I_D = 14A, L = 0.1mH, R_G = 25\Omega$	10	mJ

(1) Packaged Limited

(2) Pulse duration 10μs, duty cycle ≤2%



G006



G003



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

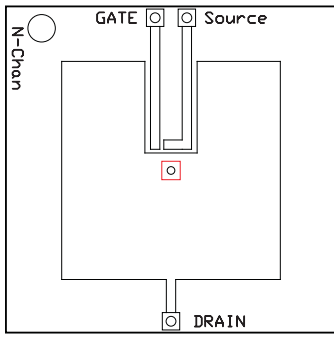
$T_A = 25^\circ\text{C}$, unless otherwise specified

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250\mu A$	0.9	1.1	1.55	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V, I_{DS} = 4A$		27	34	m Ω
		$V_{GS} = 4.5V, I_{DS} = 4A$		23	29	m Ω
		$V_{GS} = 8V, I_{DS} = 4A$		19	24	m Ω
g_{fs}	Transconductance	$V_{DS} = 15V, I_{DS} = 4A$		16.5		S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$		260	340	pF
C_{OSS}	Output Capacitance			165	215	pF
C_{RSS}	Reverse Transfer Capacitance			13	17	pF
R_g	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (4.5V)	$V_{DS} = 10V, I_{DS} = 4A$		2	2.8	nC
Q_{gd}	Gate Charge – Gate to Drain			0.4		nC
Q_{gs}	Gate Charge Gate to Source			0.6		nC
$Q_{g(th)}$	Gate Charge at V_{th}			0.3		nC
Q_{OSS}	Output Charge	$V_{DS} = 12.5V, V_{GS} = 0V$		3		nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 12.5V, V_{GS} = 4.5V, I_{DS} = 4A$ $R_G = 2\Omega$		2.7		ns
t_r	Rise Time			4.4		ns
$t_{d(off)}$	Turn Off Delay Time			4.1		ns
t_f	Fall Time			1.7		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_{DS} = 4A, V_{GS} = 0V$		0.8	1	V
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 12.5V, I_F = 4A, di/dt = 200A/\mu s$		5.1		nC
t_{rr}	Reverse Recovery Time	$V_{DD} = 12.5V, I_F = 4A, di/dt = 200A/\mu s$		11		ns

THERMAL INFORMATION

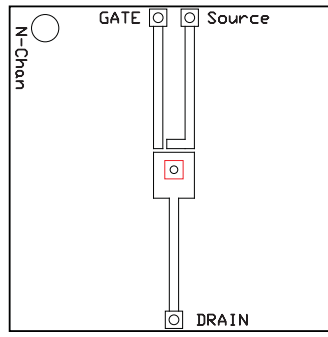
THERMAL METRIC ⁽¹⁾⁽²⁾		CSD16301Q2	UNITS
		6 PINS	
θ_{JA}	Junction-to-ambient thermal resistance ⁽³⁾⁽⁴⁾	69	$^\circ\text{C/W}$
θ_{JcTop}	Junction-to-case (top) thermal resistance ⁽³⁾	8.4	
θ_{JB}	Junction-to-board thermal resistance		
Ψ_{JT}	Junction-to-top characterization parameter		
Ψ_{JB}	Junction-to-board characterization parameter		
θ_{JcBot}	Junction-to-case (bottom) thermal resistance		

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
- (2) For thermal estimates of this device based on PCB copper area, see the [TI PCB Thermal Calculator](#).
- (3) $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
- (4) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



M0164-01

Max $R_{\theta JA} = 69^\circ\text{C/W}$
when mounted on
1 inch² (6.45 cm²) of
2-oz. (0.071-mm thick)
Cu.

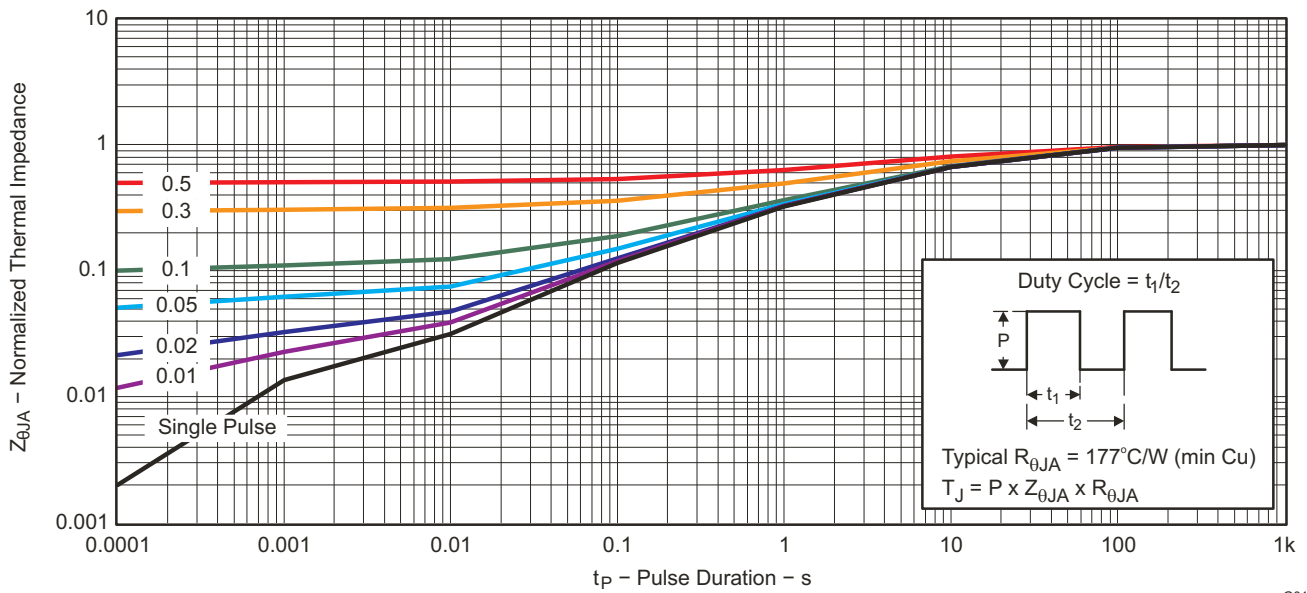


M0164-02

Max $R_{\theta JA} = 220^\circ\text{C/W}$
when mounted on
minimum pad area of
2-oz. (0.071-mm thick)
Cu.

TYPICAL MOSFET CHARACTERISTICS

$T_A = 25^\circ\text{C}$, unless otherwise specified



G012

Figure 2. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

$T_A = 25^\circ\text{C}$, unless otherwise specified

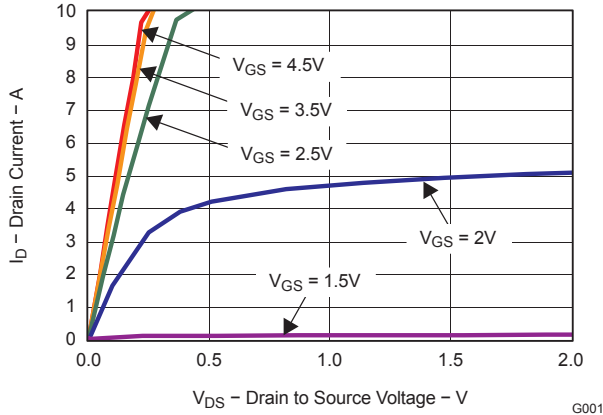


Figure 3. Saturation Characteristics

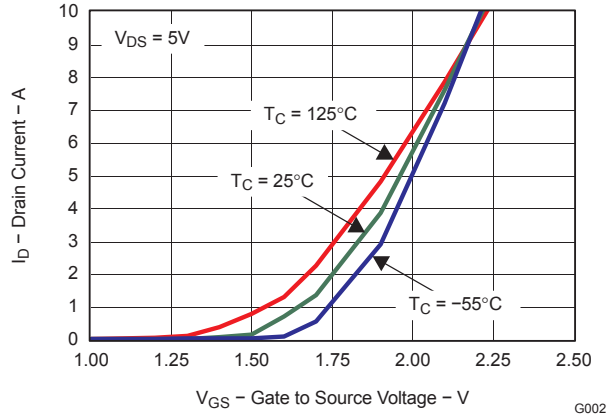


Figure 4. Transfer Characteristics

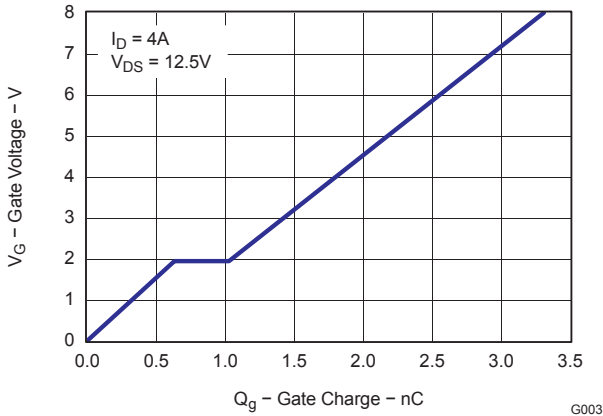


Figure 5. Gate Charge

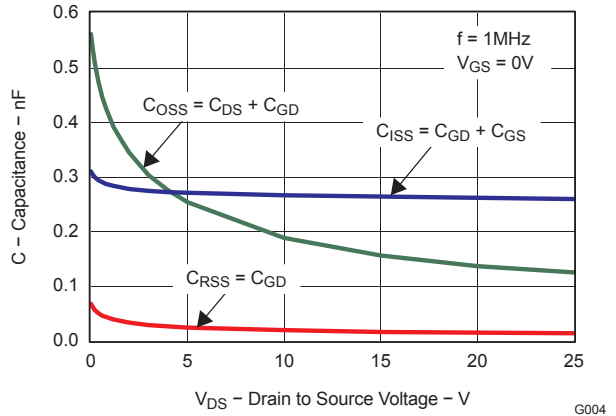


Figure 6. Capacitance

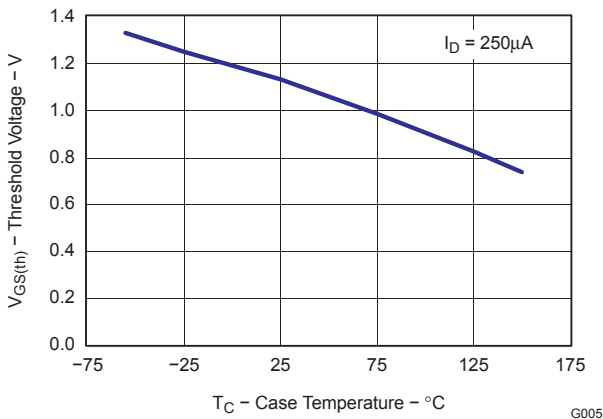


Figure 7. Threshold Voltage vs. Temperature

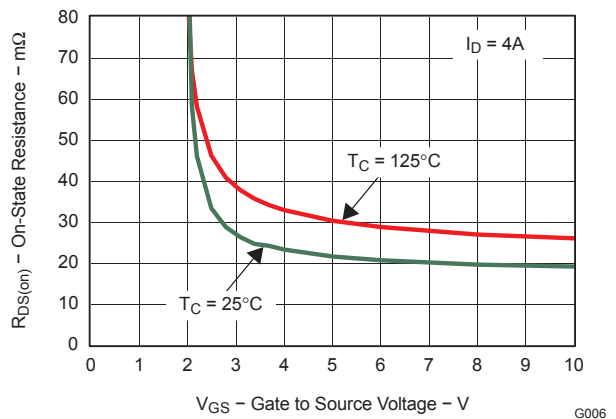


Figure 8. On-State Resistance vs. Gate to Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

$T_A = 25^\circ\text{C}$, unless otherwise specified

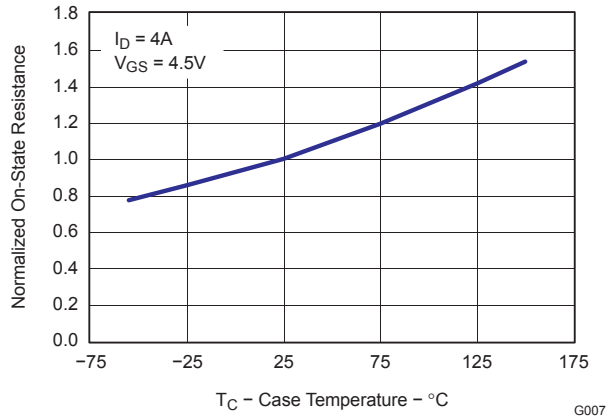


Figure 9. Normalized On-State Resistance vs. Temperature

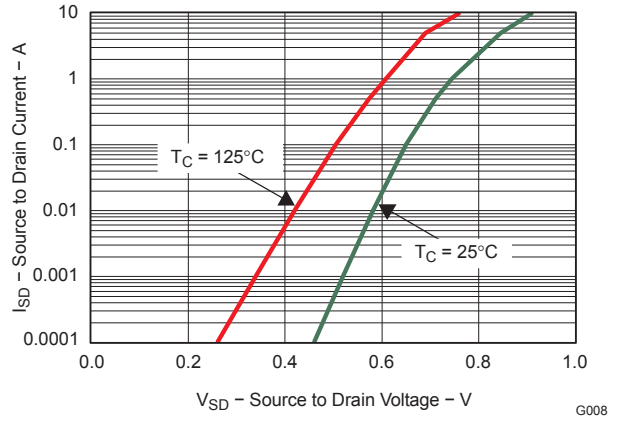


Figure 10. Typical Diode Forward Voltage

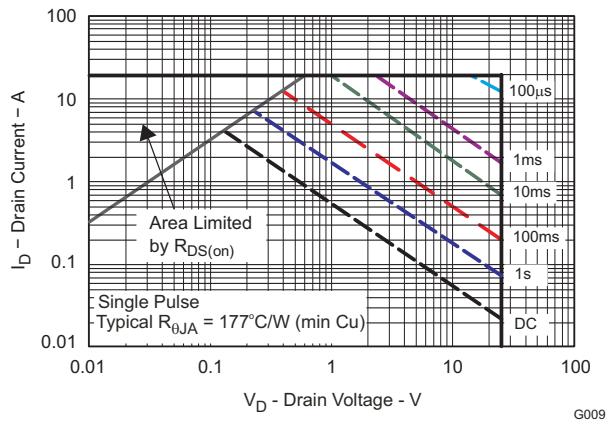


Figure 11. Maximum Safe Operating Area

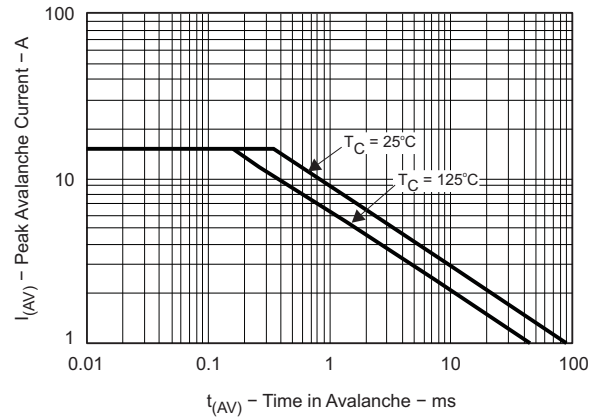


Figure 12. Single Pulse Unclamped Inductive Switching

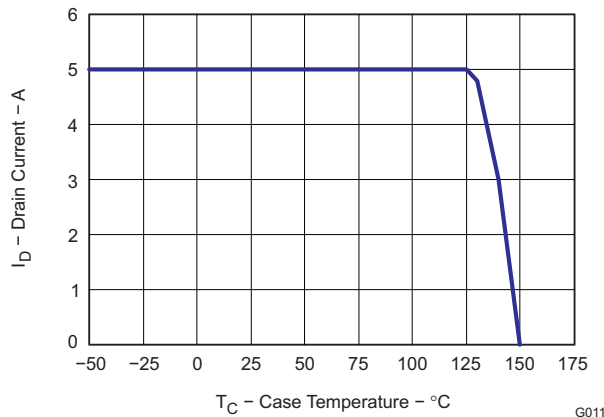
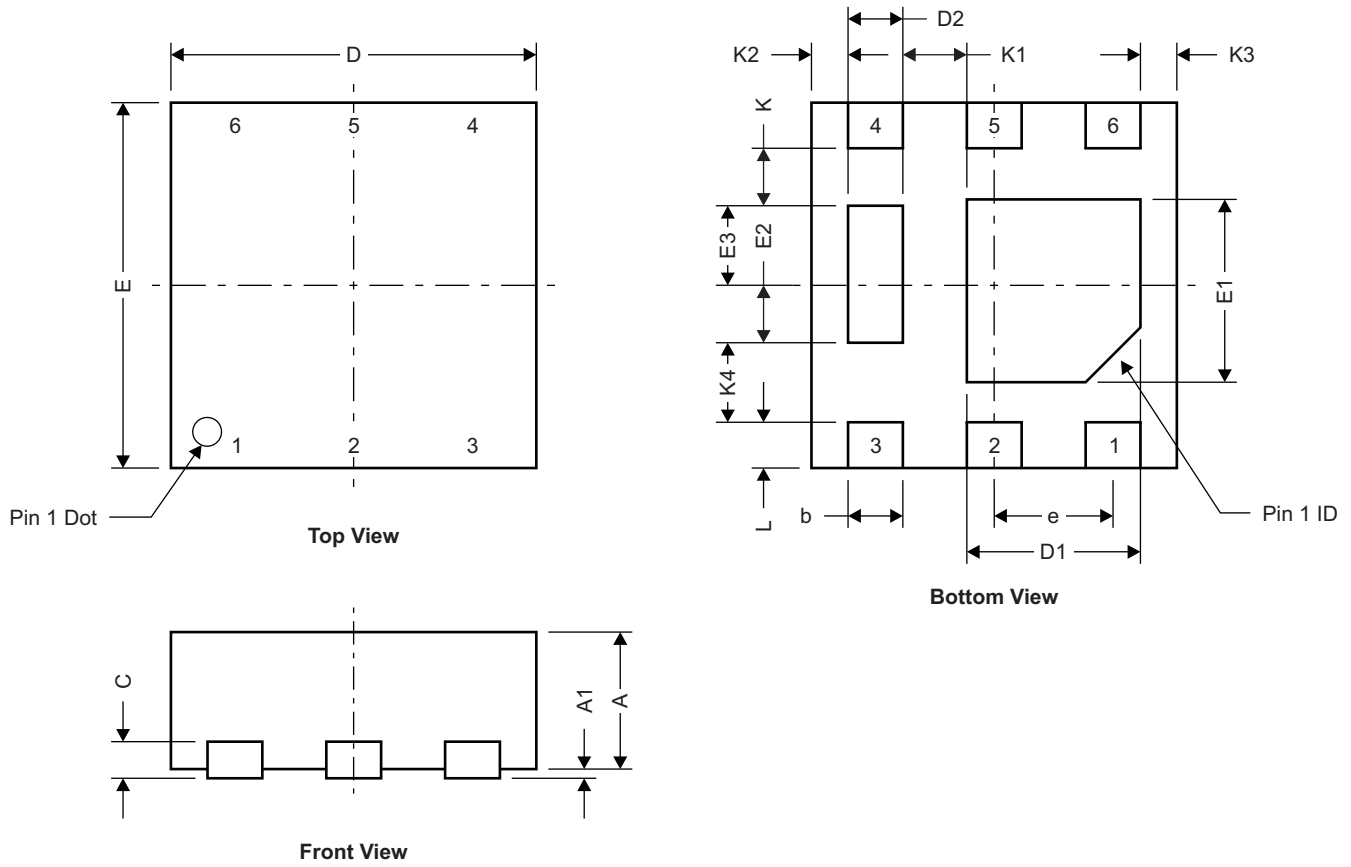


Figure 13. Maximum Drain Current vs. Temperature

MECHANICAL DATA

Q2 Package Dimensions



M0165-01

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.032
A1	0.000		0.050	0.000		0.002
b	0.250	0.300	0.350	0.010	0.012	0.014
C	0.203 TYP			0.008 TYP		
D	2.000 TYP			0.080 TYP		
D1	0.900	0.950	1.000	0.036	0.038	0.040
D2	0.300 TYP			0.012 TYP		
E	2.000 TYP			0.080 TYP		
E1	0.900	1.000	1.100	0.036	0.040	0.044
E2	0.280 TYP			0.0112 TYP		
E3	0.470 TYP			0.0188 TYP		
e	0.650 BSC			0.026 TYP		
K	0.280 TYP			0.0112 TYP		
K1	0.350 TYP			0.014 TYP		
K2	0.200 TYP			0.008 TYP		
K3	0.200 TYP			0.008 TYP		
K4	0.470 TYP			0.0188 TYP		
L	0.200	0.25	0.300	0.008	0.010	0.012

REVISION HISTORY

Changes from Original (October 2009) to Revision A **Page**

- Changed the Electrical Characteristics table - $V_{GS(th)}$ MAX value From: 1.4V To 1.55V **2**
-

Changes from Revision A (December 2009) to Revision B **Page**

- Added title to [Figure 12](#) - Single Pulse Unclamped Inductive Switching **5**
 - Deleted the Package Marking Information section **7**
-

Changes from Revision B (April 2010) to Revision C **Page**

- Added a 7-Inch Reel option to the Ordering Information Table **1**
-

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16301Q2	WSON	DQK	6	3000	180.0	8.4	2.3	2.3	1.0	4.0	2.3	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16301Q2	WSON	DQK	6	3000	550.0	455.0	55.0

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